



wherein $\text{M}=\text{H}, \text{NH}_4, \text{Na}, \text{Li}, \text{K}$ and n can range between 2 and 5.

5. (Amended) A formulation according to claim 1, wherein the non ionic fluorinated surfactants added to the PTFE polymerization latex have the following structures:



wherein:

R_f is selected from the structures (a), (b), (c), (d), (e), (f) of claim 2;

L is a divalent organic group, a linking group between R_f and R_h , selected from: $-\text{CO}-\text{NR}^1-$, $-\text{CH}_2(\text{OCH}_2\text{CHR}^2)_a-\text{O}-$, $-\text{CH}_2(\text{OCH}_2\text{CHR}^2)_b-\text{O}-\text{CO}-$, $-\text{CH}_2\text{O}-(\text{CH}_2)_c-\text{CO}-\text{O}-$, $-\text{CH}_2-\text{CH}_2-\text{O}-$, $-\text{CH}_2-\text{CH}_2-$; wherein R^1 is $-\text{H}$ or a C_1-C_4 alkyl; R^2 is $-\text{H}$ or a C_1-C_2 alkyl; a, b are numbers from 0 to 6, preferably from 0 to 2; c is a number from 1 to 3;

R_h is a radical having a polyoxyalkylene structure selected from:

- (i) $-(\text{CH}_2\text{CH}_2\text{O})_q\text{CH}_2\text{CH}_2\text{Z}$, wherein: q is an integer from 5 to 70, preferably from 6 to 25; Z is selected from $-\text{OH}$, C_1-C_4 alkoxy;
- (ii) $-(\text{CH}_2\text{CH}_2\text{O})_r(\text{CH}_2\text{CH}(\text{CH}_3)\text{O})_s\text{CH}_2\text{CHR}^3\text{Z}$, wherein $r+s$ is an integer from 5 to 70, preferably from 10 to 50; the r/s ratio is in the range 0.1-10, preferably 0.5-5; R^3 is selected between $-\text{H}$ and $-\text{CH}_3$; Z is selected between $-\text{OH}$, C_1-C_4 alkoxy.

A2 7. (Amended) A formulation according to claim 1, wherein the PTFE is modified with one or more comonomers containing at least one unsaturation of ethylene type in an amount up to 6% molar, preferably up to 1% molar.

A3 12. (Amended) Dielectric films obtained from the formulation according to claim 1, by the deposition of the formulation on a substratum, subsequent film sintering at a temperature higher than the PTFE melting T and subsequent air-cooling.

A4 14. (Amended) Dielectric films according to claim 12 having a thickness lower than 200 nm, preferably in the range 50 nm - 150 nm, a dielectric constant lower than 2.2, a dielectric strength higher than 4 MV/cm and a weight loss at 425°C in the range 0.0008 - 0.02%/min.

15. (Amended) Use of dielectric films according to claim 12 for the insulation of conductors in integrated circuits.

REMARKS

Claims 1-15 are pending in this application. By this Amendment, claims 4, 5, 7, 12, 14, and 15 are amended to delete multiple dependency. No new matter is contained in the amendments. Timely examination on the merits is respectfully requested.